

preliminary

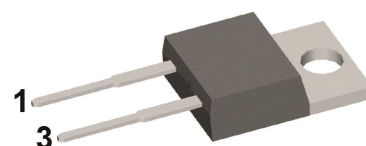
Sonic Fast Recovery Diode

V_{RRM}	=	1200 V
I_{FAV}	=	20 A
t_{rr}	=	200 ns

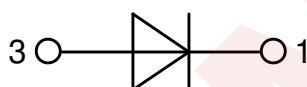
High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Single Diode

Part number

DHG20I1200PA



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220

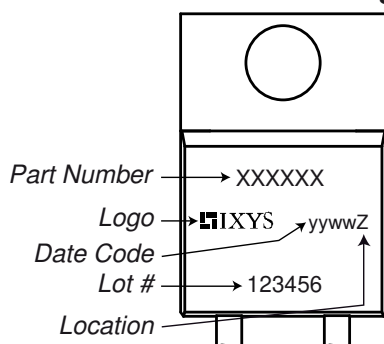
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

Fast Diode				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				1200	V	
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				1200	V	
I _R	reverse current, drain current	V _R = 1200 V	T _{VJ} = 25°C			30	μA	
		V _R = 1200 V	T _{VJ} = 125°C			0.4	mA	
V _F	forward voltage drop	I _F = 20 A	T _{VJ} = 25°C			2.24	V	
		I _F = 40 A				2.90	V	
		I _F = 20 A	T _{VJ} = 125°C			2.25	V	
		I _F = 40 A				3.17	V	
I _{FAV}	average forward current	T _C = 95°C rectangular d = 0.5	T _{VJ} = 150°C			20	A	
V _{F0}	threshold voltage	} for power loss calculation only		T _{VJ} = 150°C		1.25	V	
r _F	slope resistance					45	mΩ	
R _{thJC}	thermal resistance junction to case					0.9	K/W	
R _{thCH}	thermal resistance case to heatsink				0.5		K/W	
P _{tot}	total power dissipation	T _C = 25°C				140	W	
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		150	A	
C _J	junction capacitance	V _R = 600 V f = 1 MHz		T _{VJ} = 25°C		8	pF	
I _{RM}	max. reverse recovery current	} I _F = 20 A; V _R = 600 V -di _F /dt = 400 A/μs		T _{VJ} = 25 °C		15	A	
				T _{VJ} = 125 °C		20	A	
t _{rr}	reverse recovery time			T _{VJ} = 25 °C		200	ns	
				T _{VJ} = 125 °C		350	ns	

Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-55		150	°C
T_{op}	operation temperature		-55		125	°C
T_{stg}	storage temperature		-55		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

Product Marking

Part description

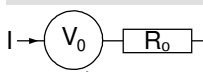
D = Diode
 H = Sonic Fast Recovery Diode
 G = extreme fast
 20 = Current Rating [A]
 I = Single Diode
 1200 = Reverse Voltage [V]
 PA = TO-220AC (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG20I1200PA	DHG20I1200PA	Tube	50	504934

Similar Part	Package	Voltage class
DHG20I1200HA	TO-247AD (2)	1200

Equivalent Circuits for Simulation

* on die level

 $T_{VJ} = 150^{\circ}\text{C}$

Fast Diode
 $V_{0\max}$ threshold voltage

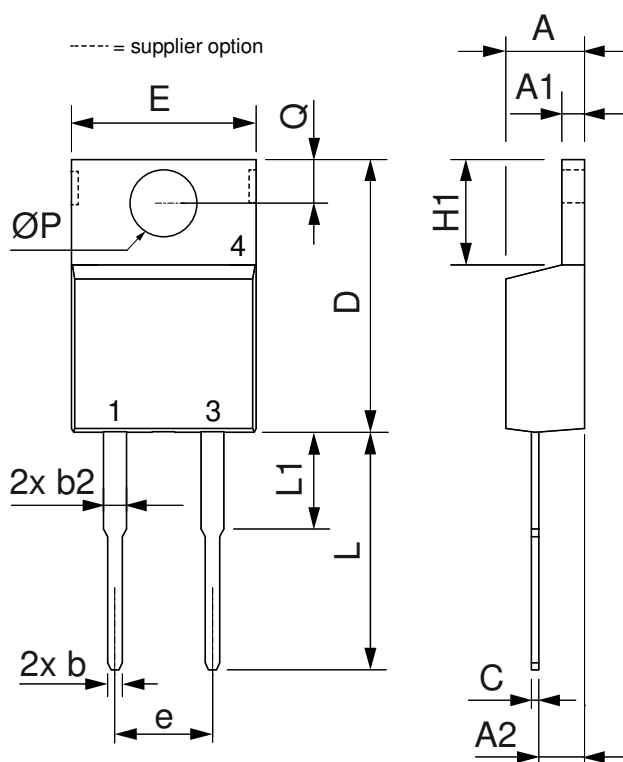
1.25

V

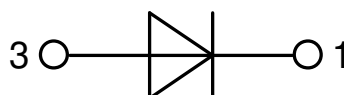
 $R_{0\max}$ slope resistance *

42

mΩ

Outlines TO-220


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



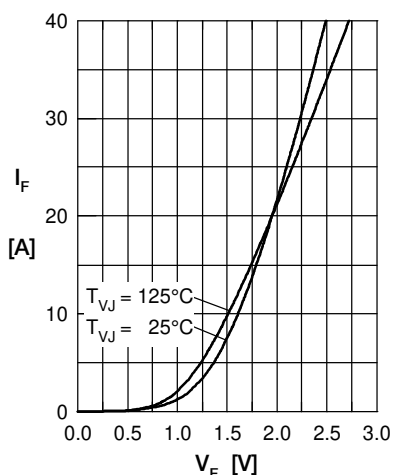
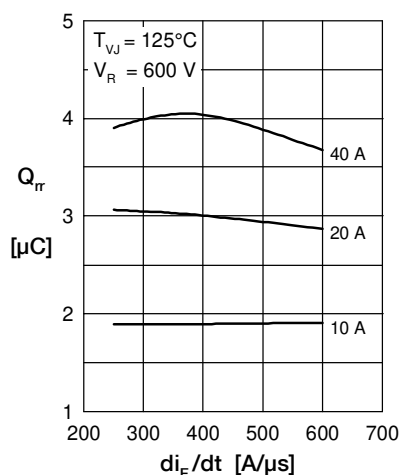
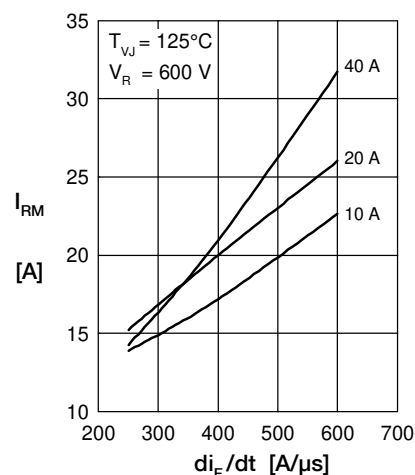
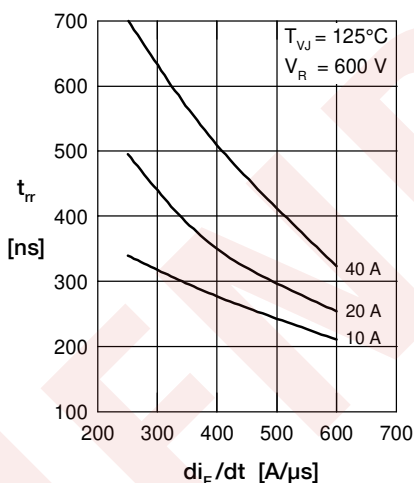
Fast Diode

 Fig. 1 Typ. Forward current versus V_F

 Fig. 2 Typ. reverse recov. charge Q_{rr} versus di_F/dt

 Fig. 3 Typ. peak reverse current I_{RM} versus di_F/dt

 Fig. 4 Dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

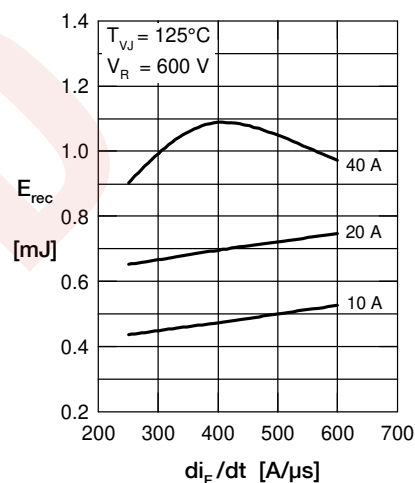
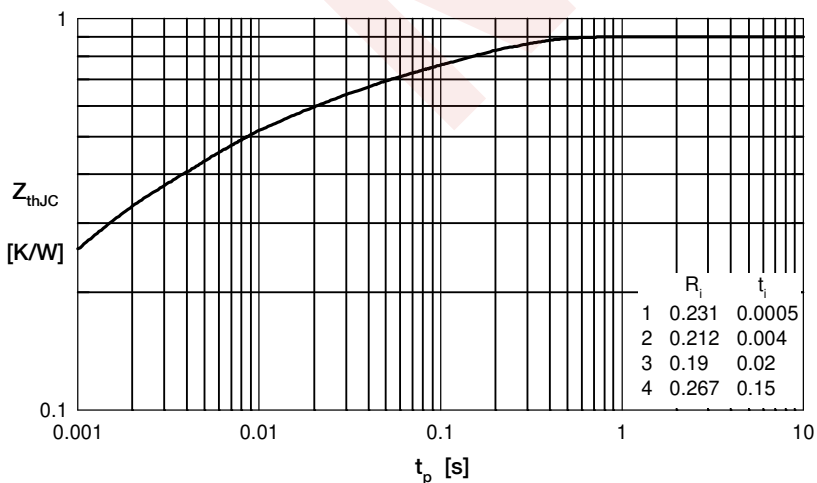
 Fig. 5 Typ. recovery time t_{rr} versus di_F/dt

 Fig. 6 Typ. recovery energy E_{rec} versus di_F/dt


Fig. 7 Typ. transient thermal impedance junction to case